

FIG. 1

FIG. 2-(1)

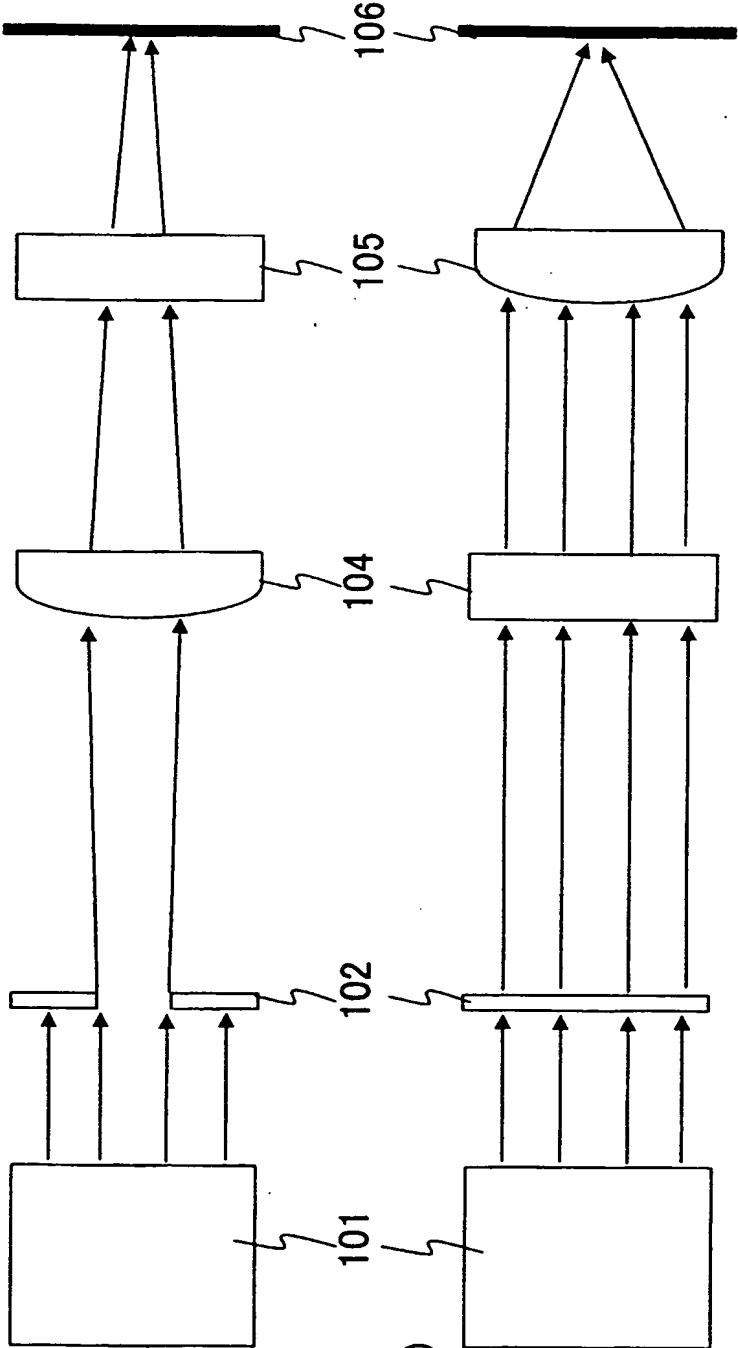
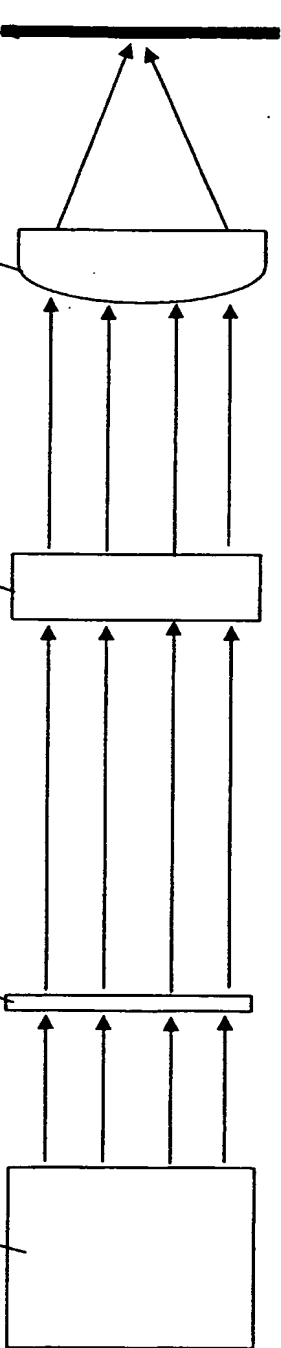


FIG. 2-(2)



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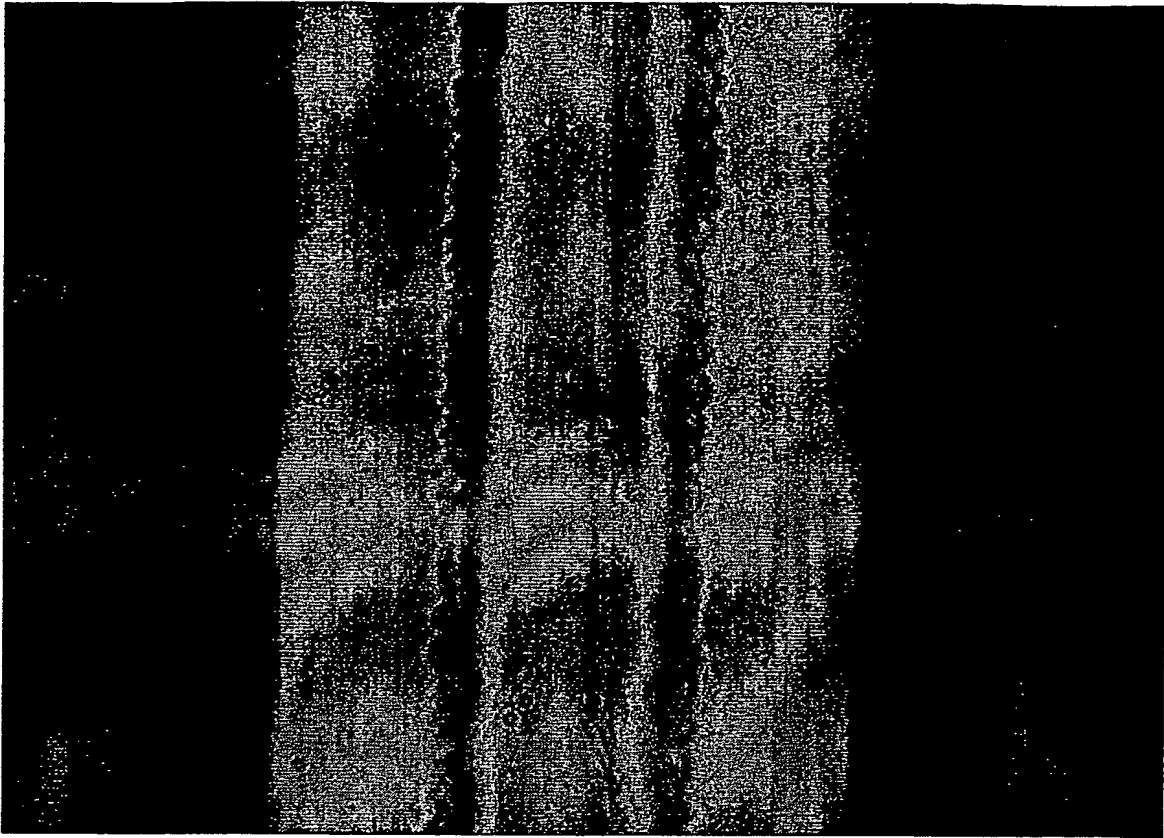


FIG. 3

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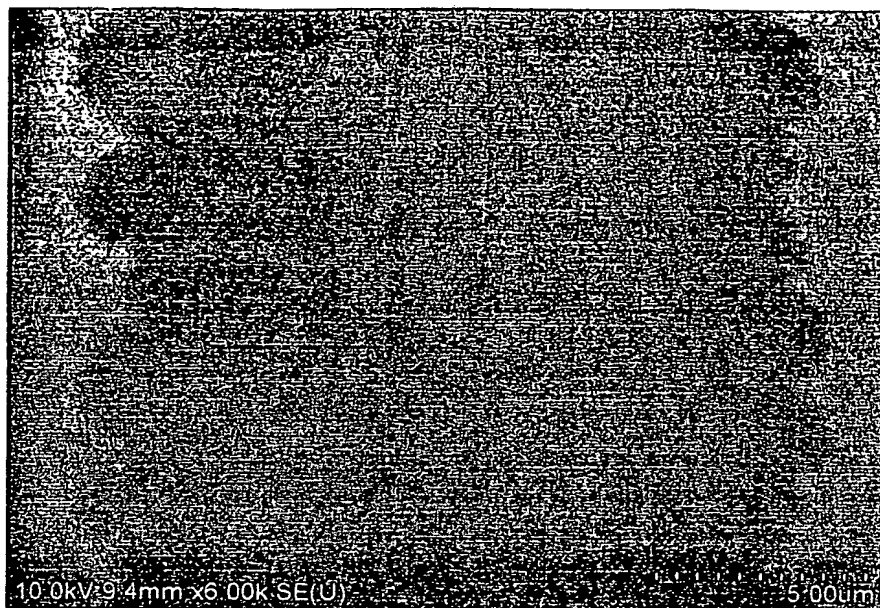


FIG. 4

FIG. 5A

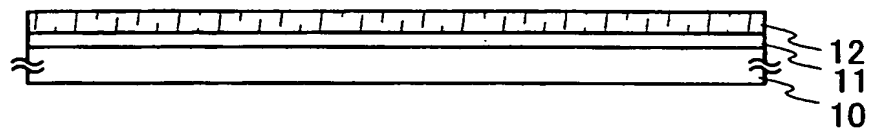


FIG. 5B

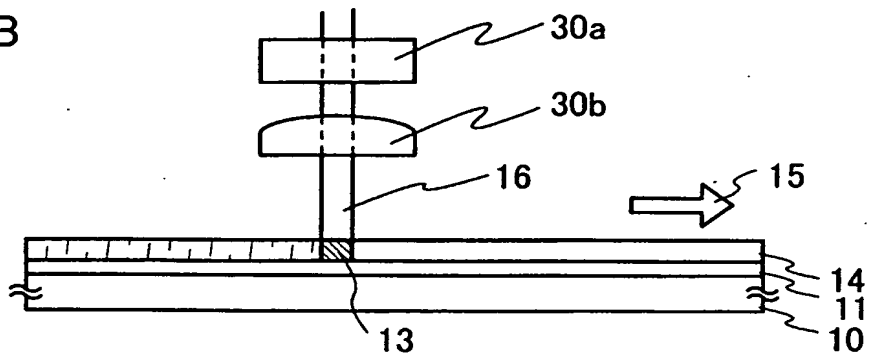


FIG. 5C

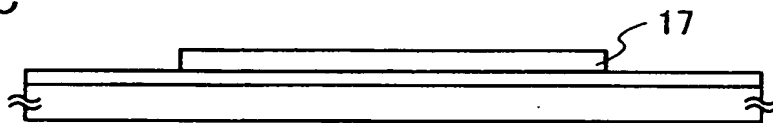


FIG. 5D

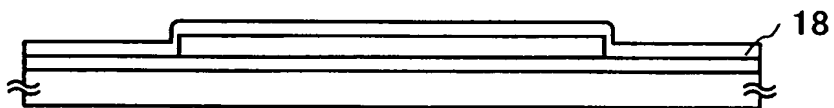
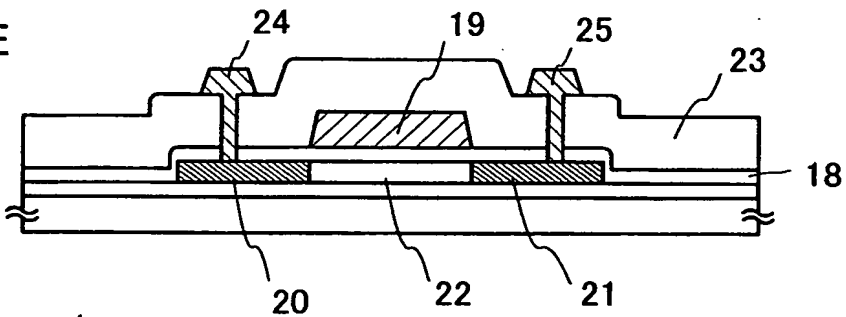


FIG. 5E



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FIG. 6A

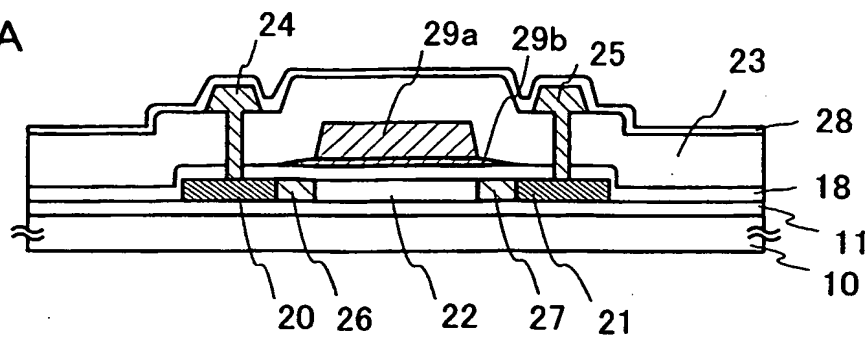
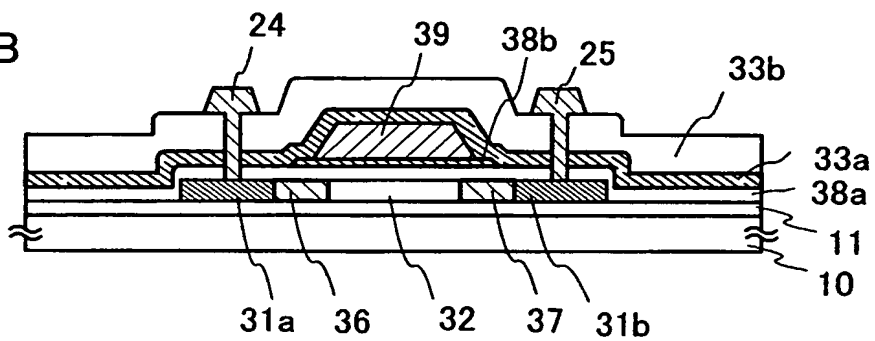


FIG. 6B



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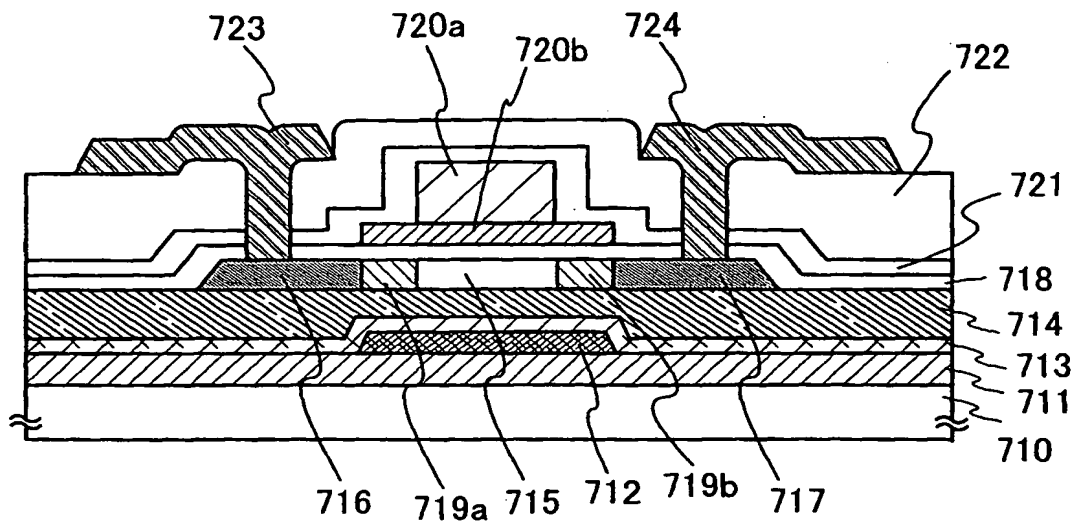


FIG. 7

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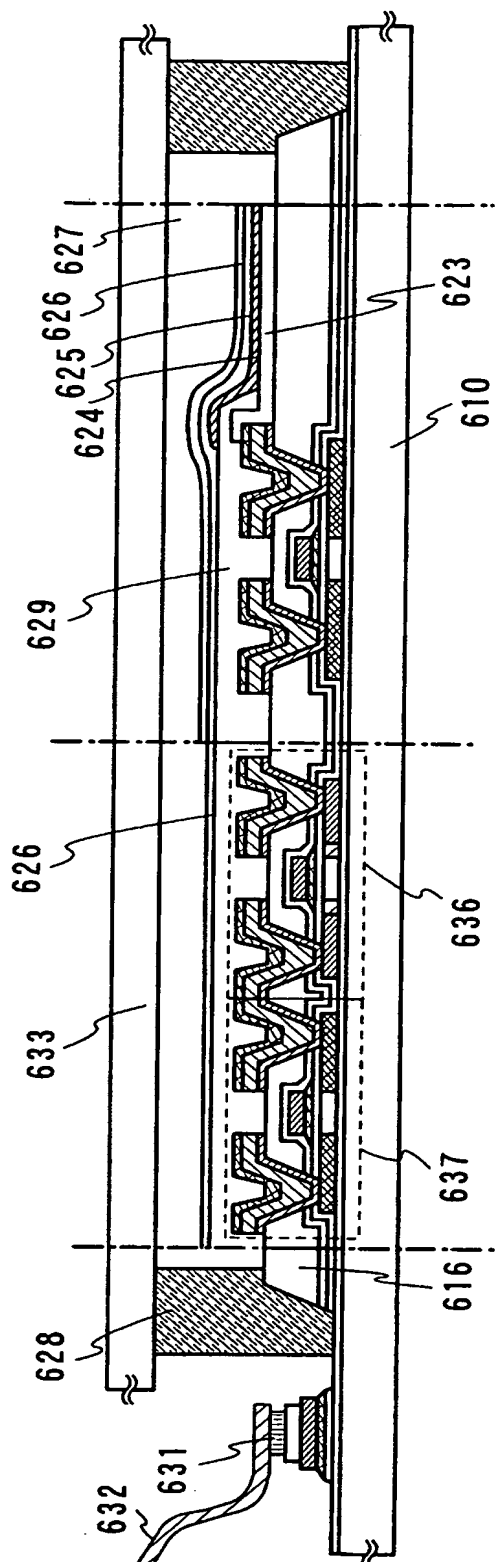


FIG. 8

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FIG. 9A

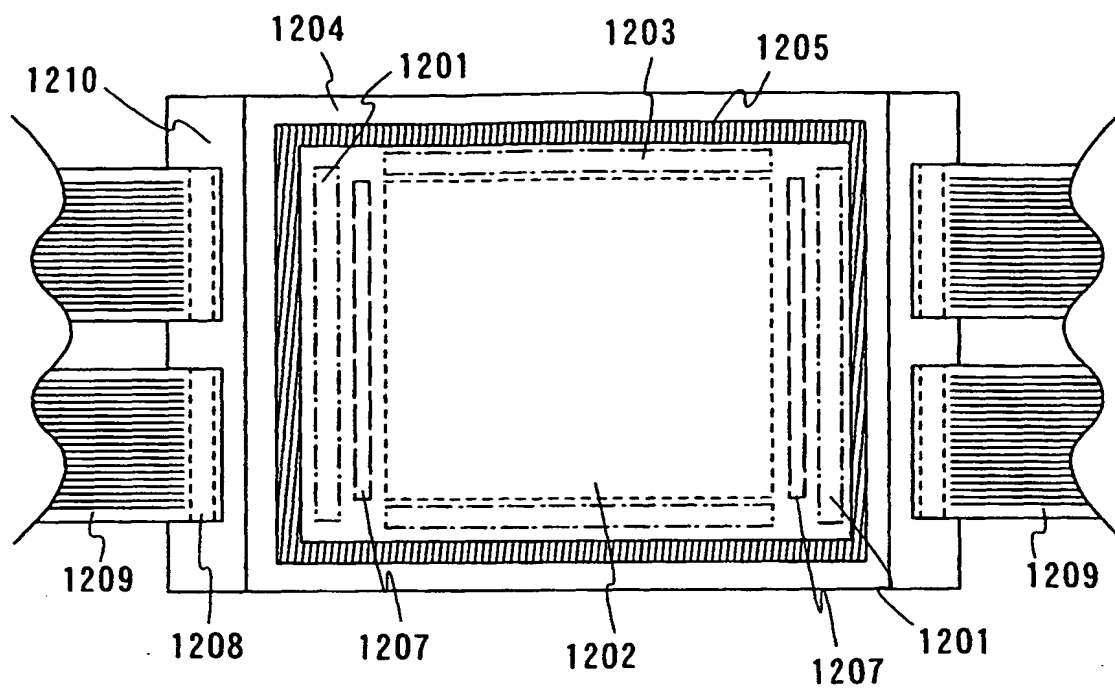
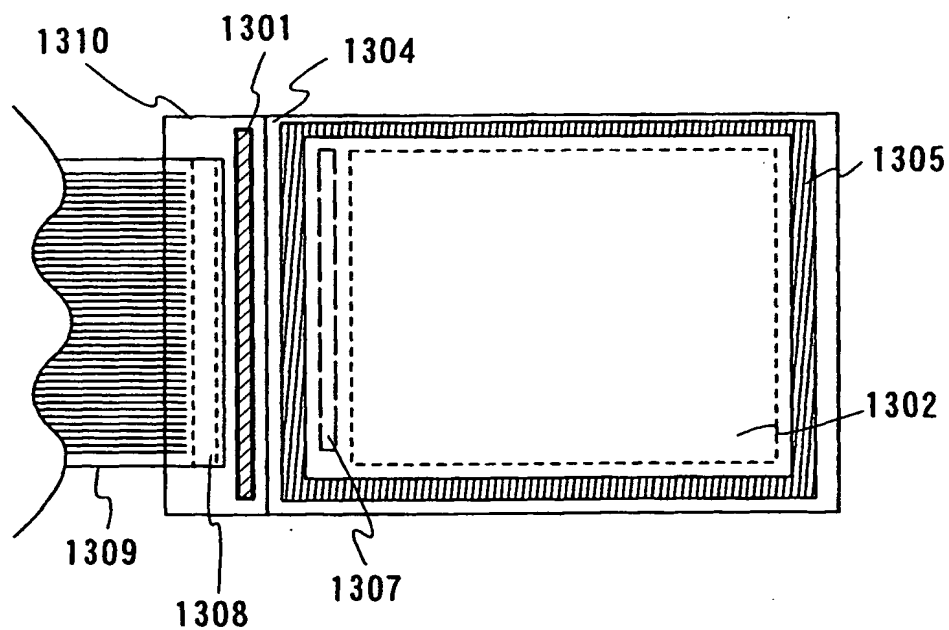


FIG. 9B



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FIG. 10A

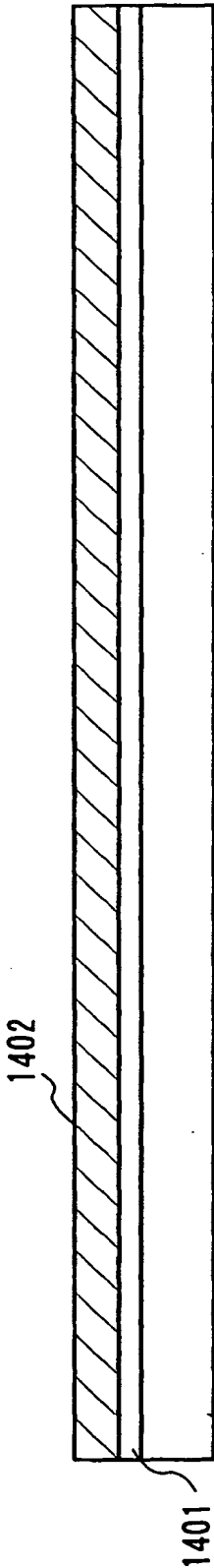


FIG. 10B

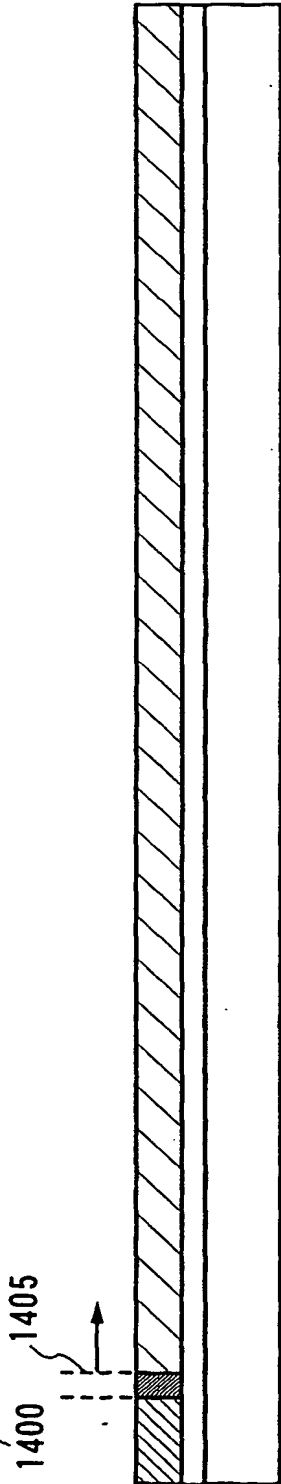
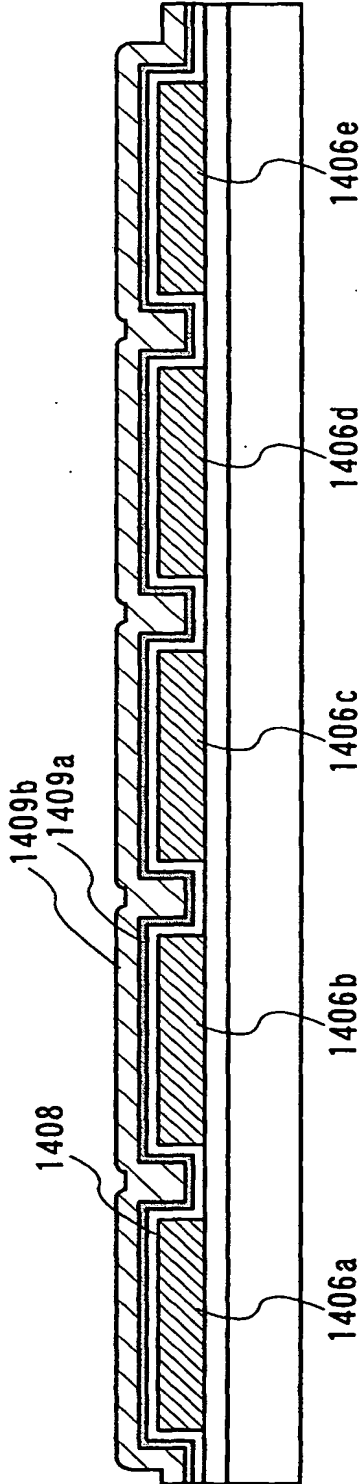


FIG. 10C



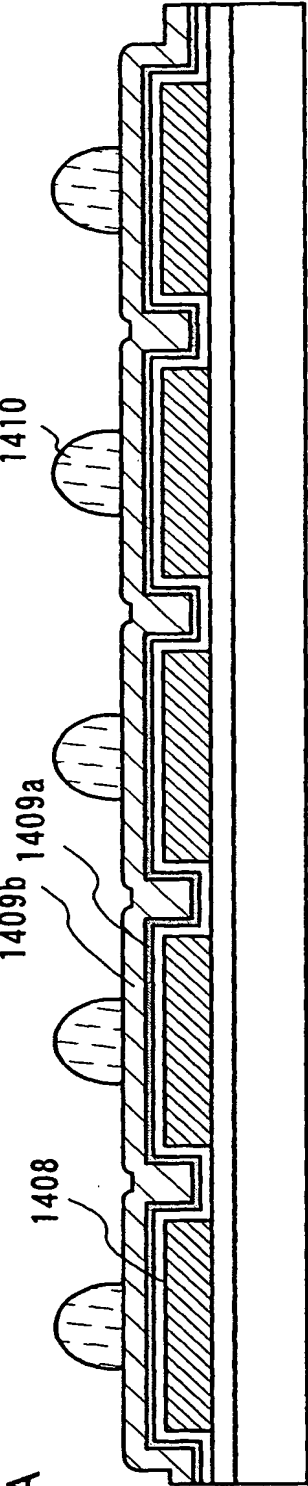


FIG. 11A

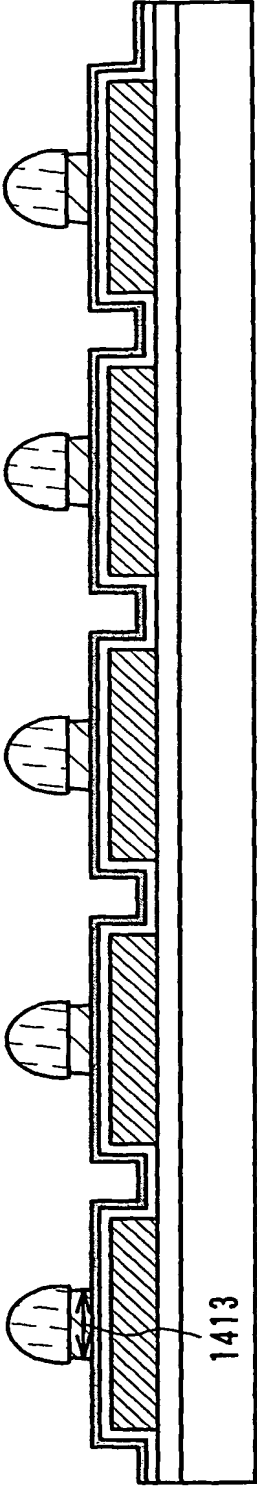


FIG. 11B

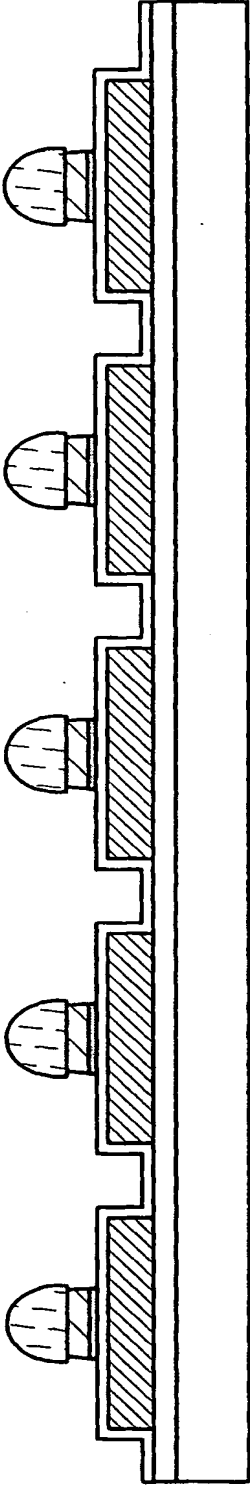


FIG. 11C

FIG. 12A

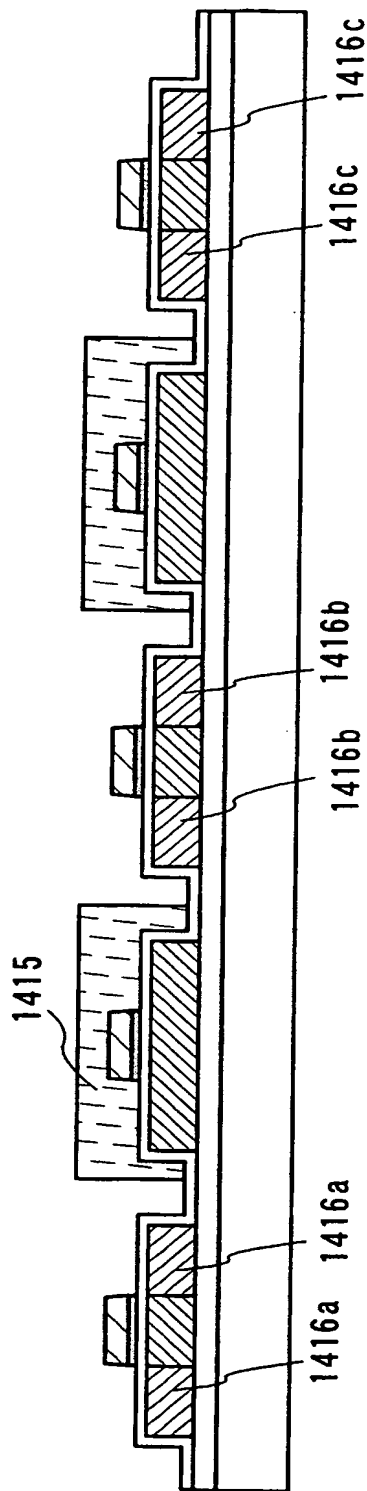


FIG. 12B

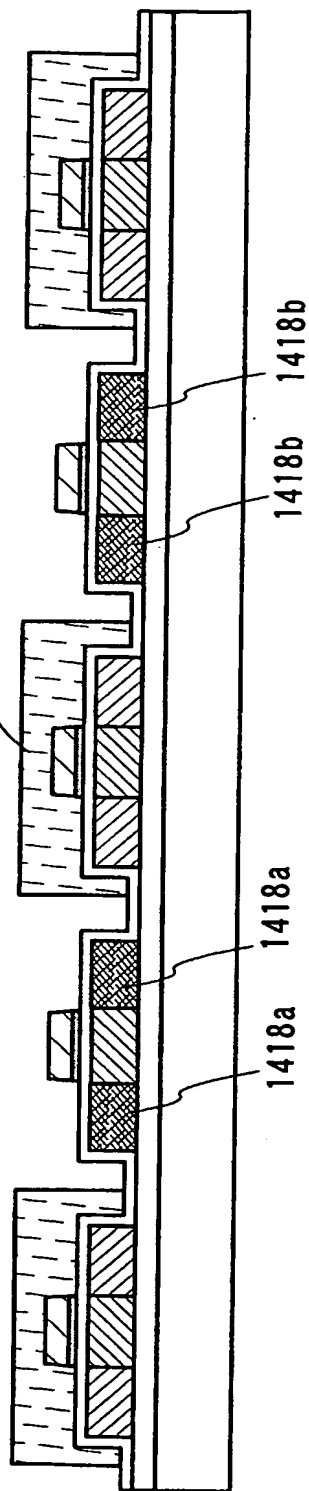


FIG. 12C

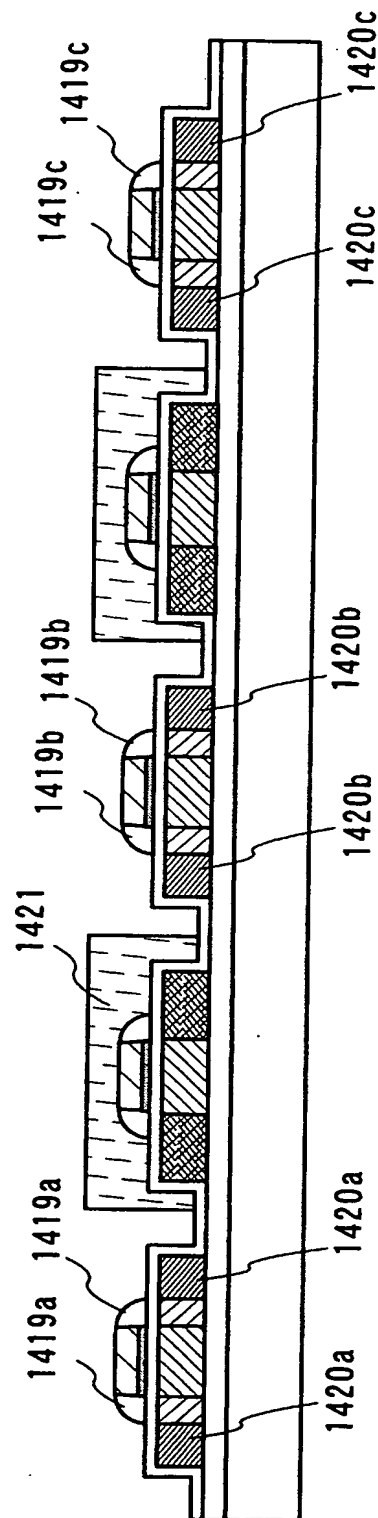


FIG. 13A

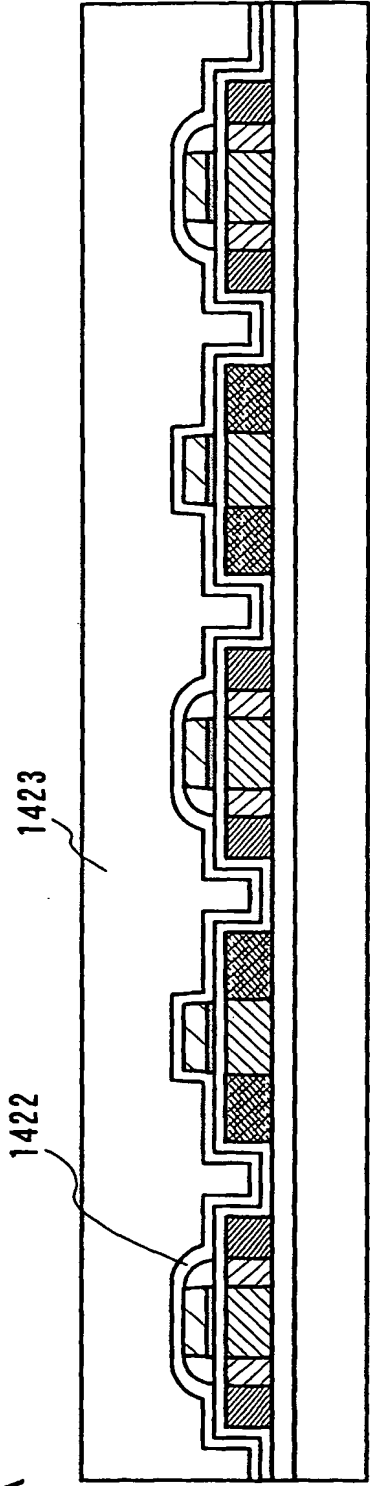
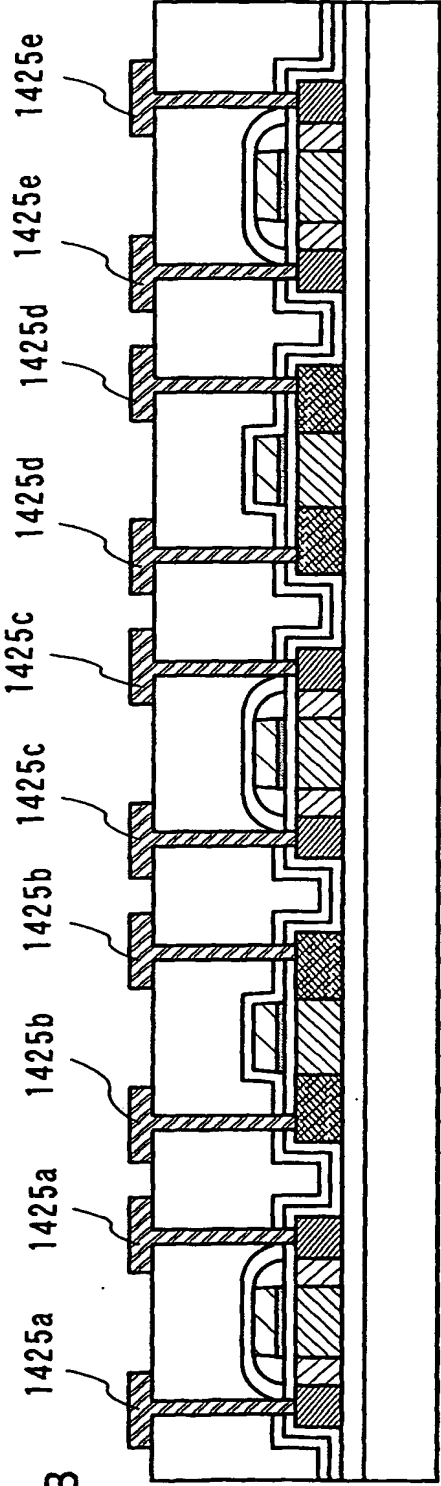


FIG. 13B



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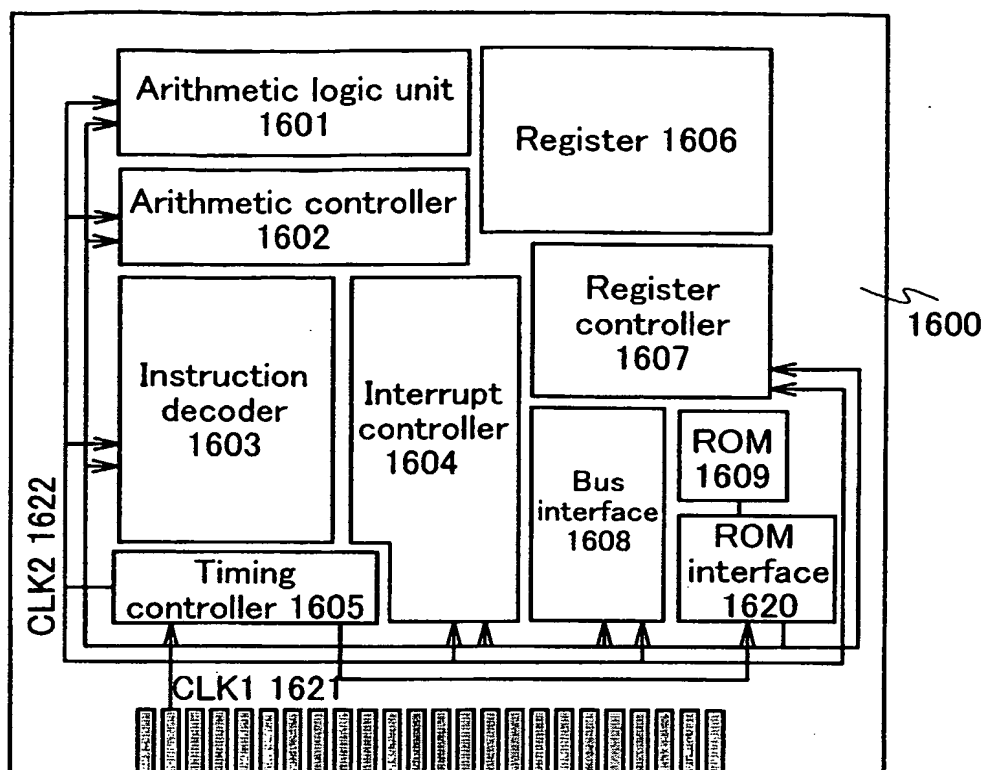


FIG. 14

FIG. 15A

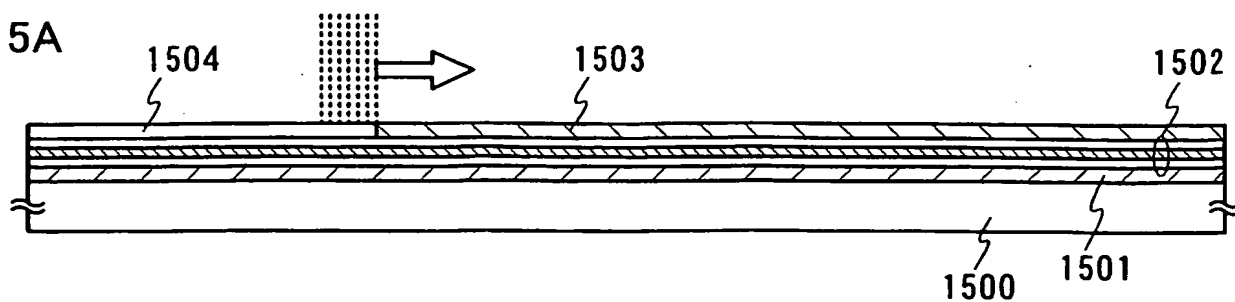


FIG. 15B

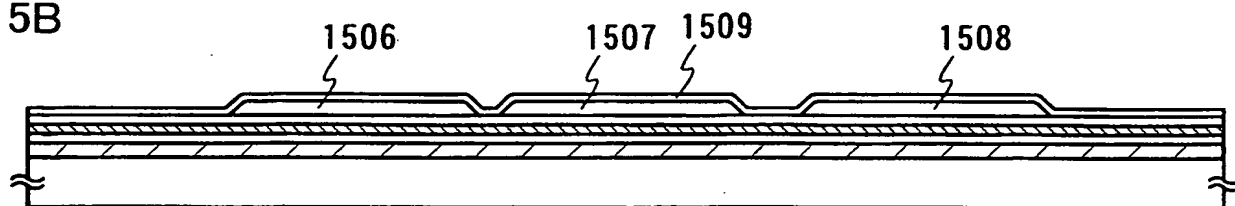


FIG. 15C

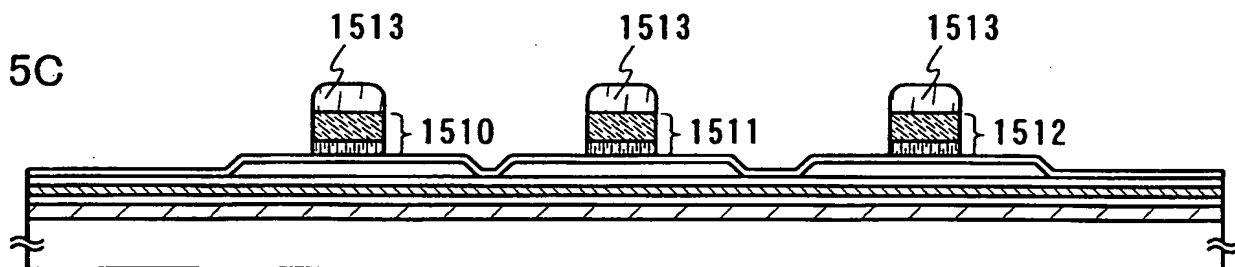


FIG. 15D

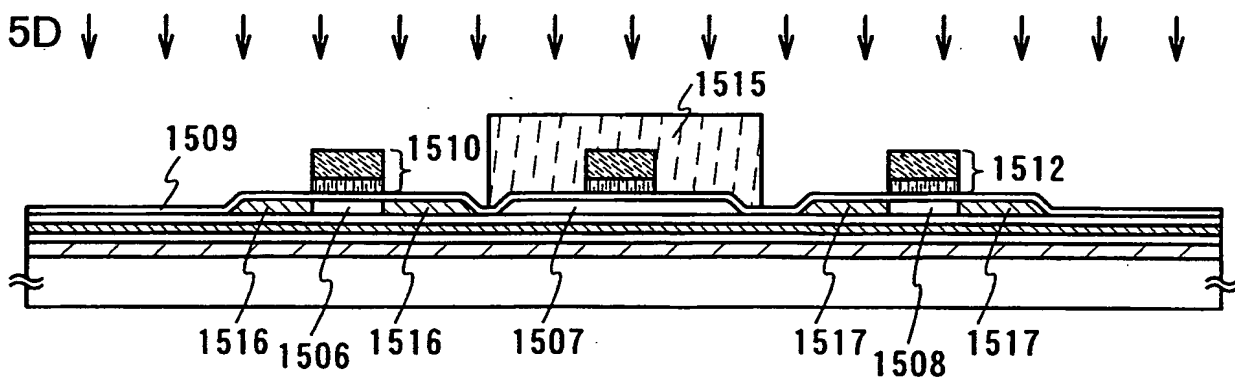
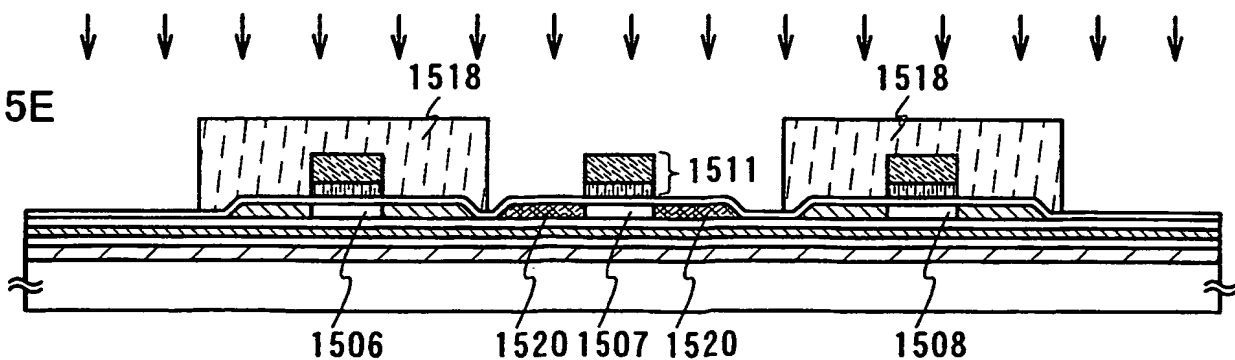


FIG. 15E



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FIG. 16A

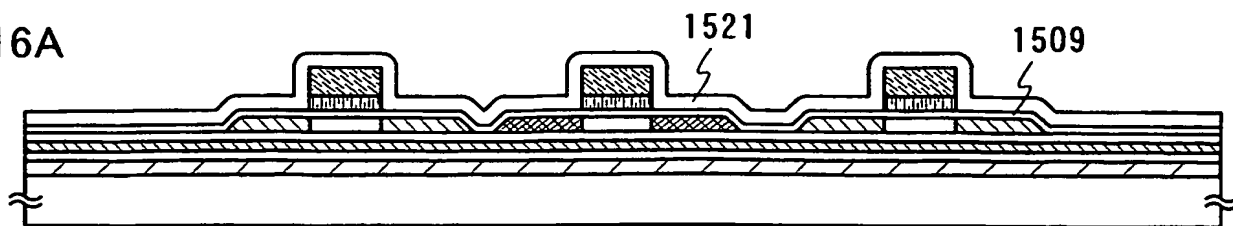


FIG. 16B

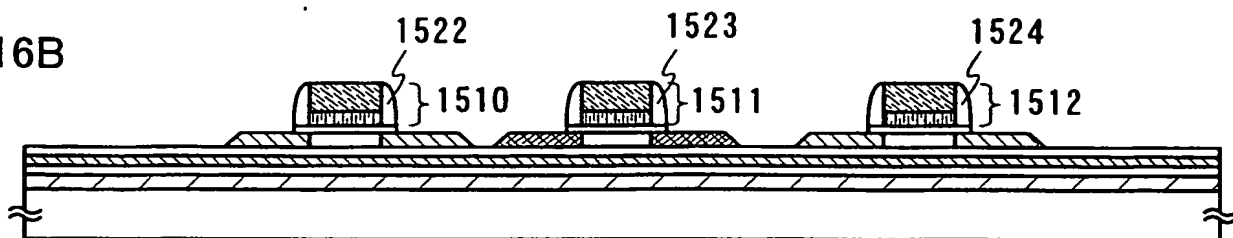


FIG. 16C

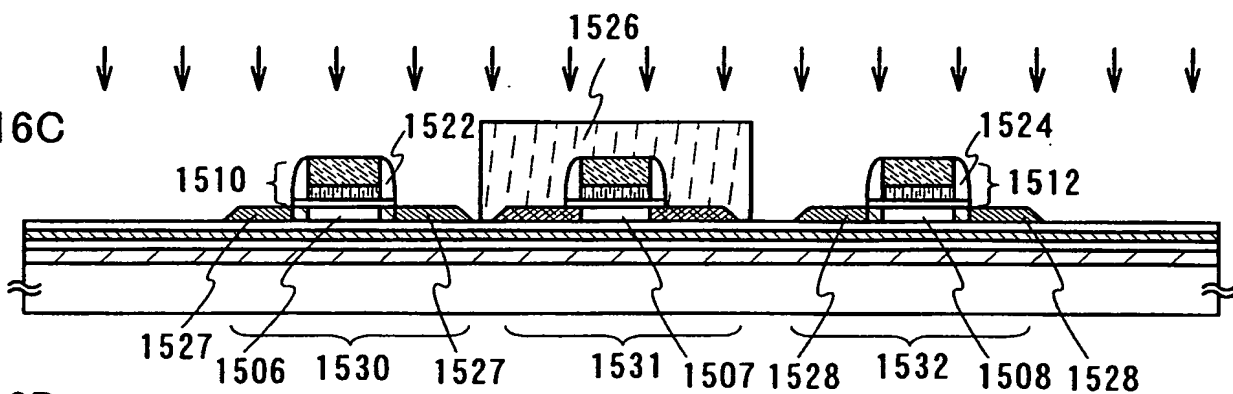


FIG. 16D

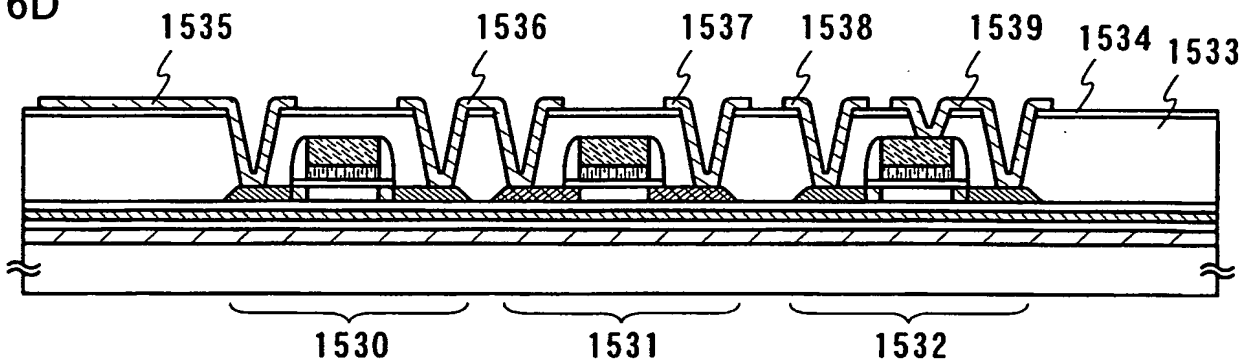


FIG. 16E

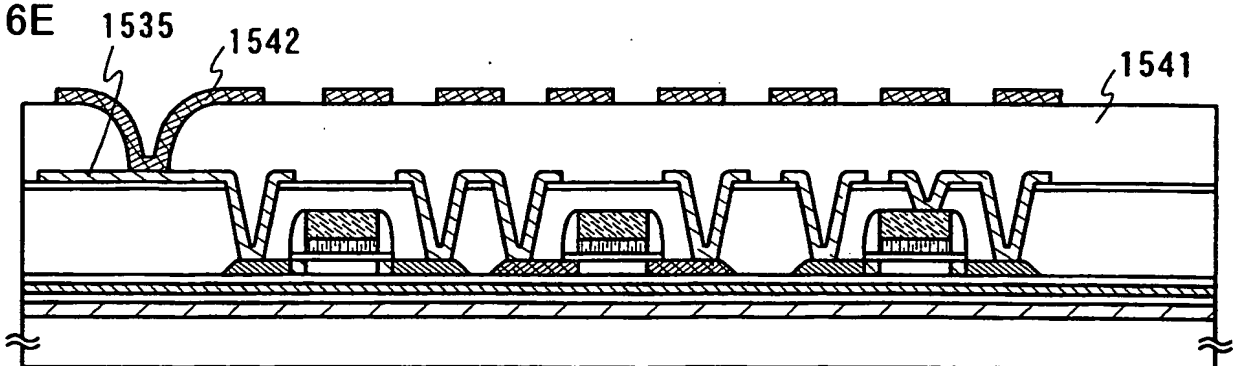


FIG. 17A

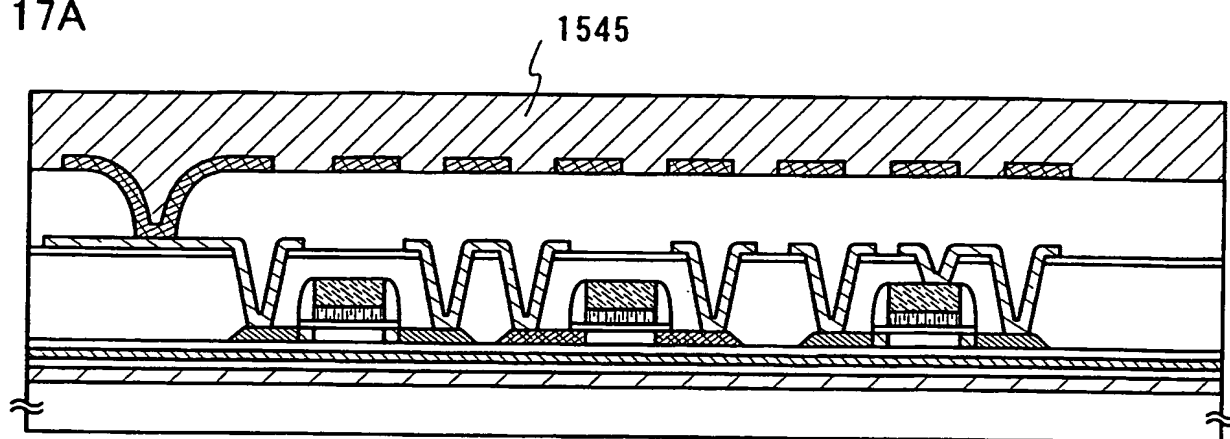


FIG. 17B

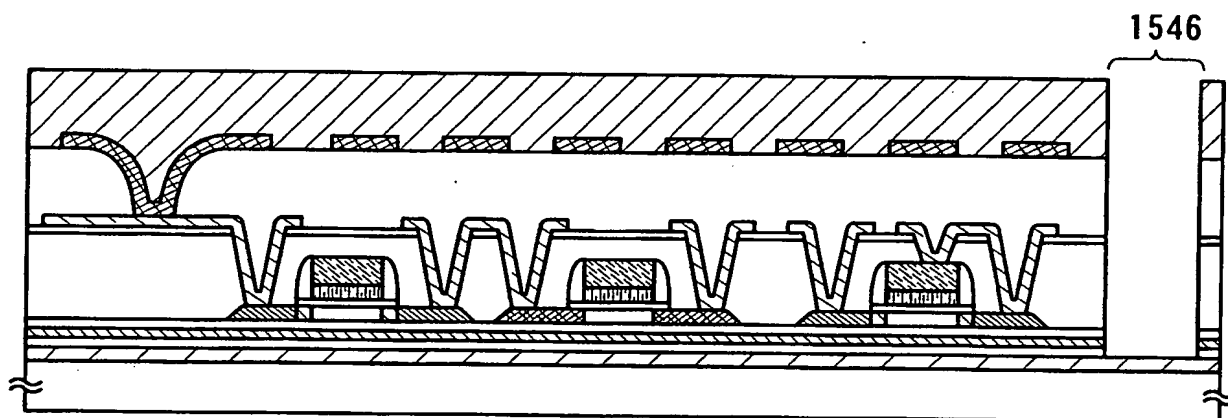


FIG. 17C

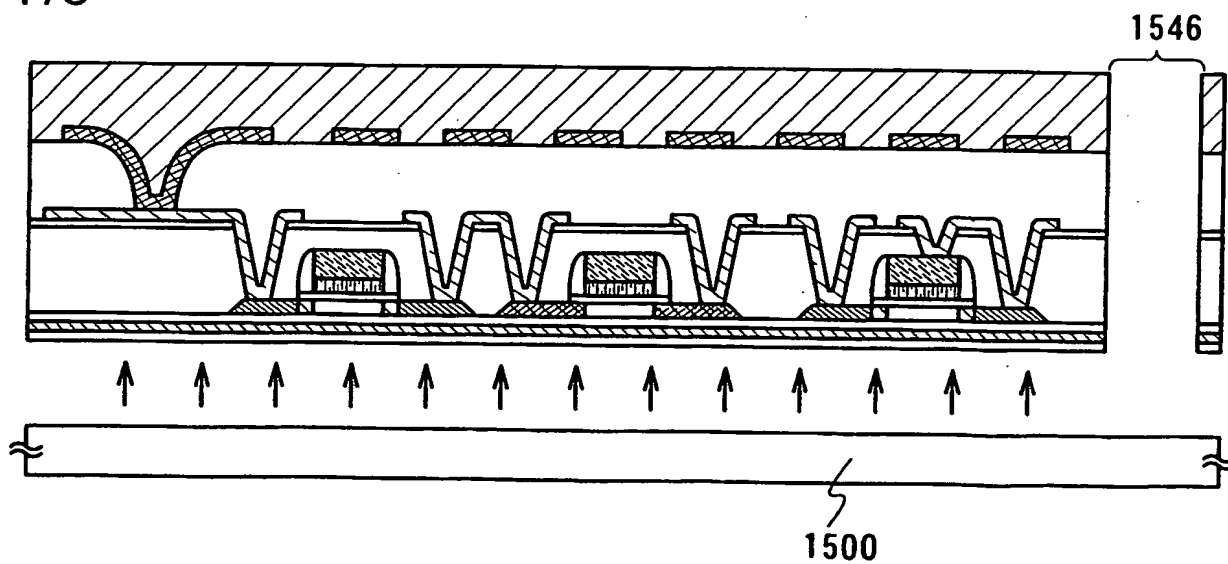


FIG. 18A

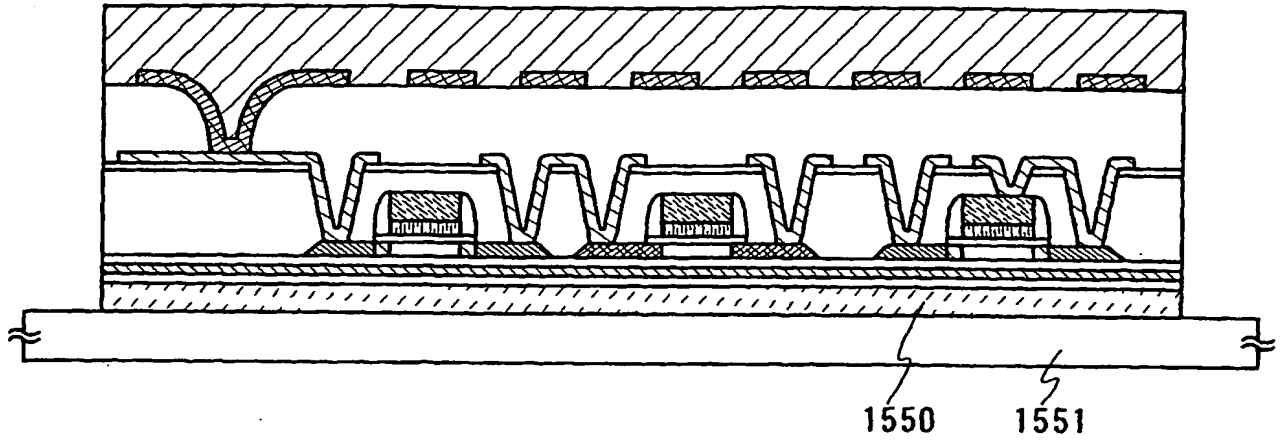
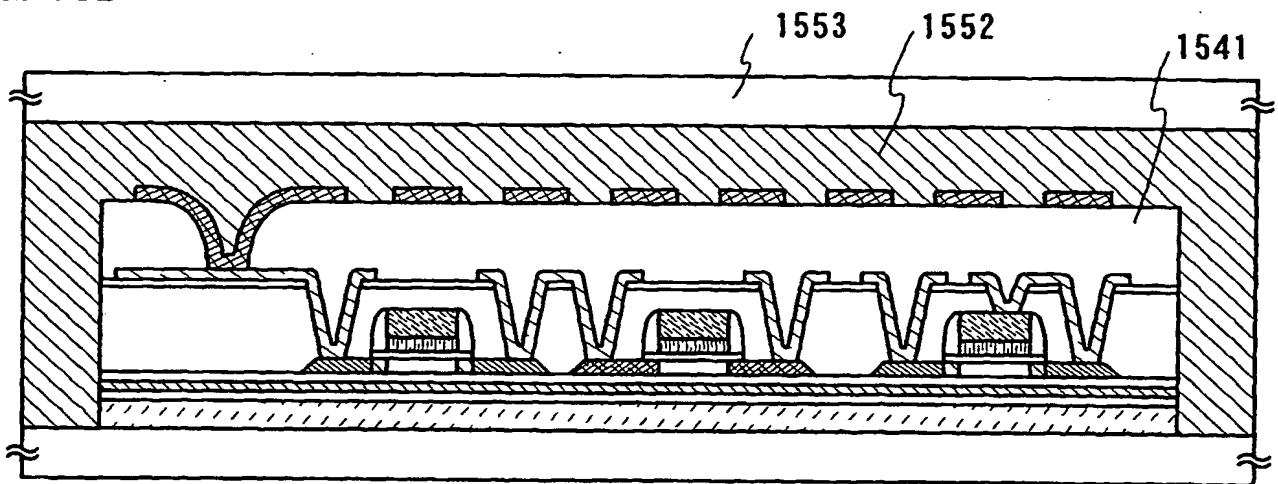


FIG. 18B



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FIG. 19A

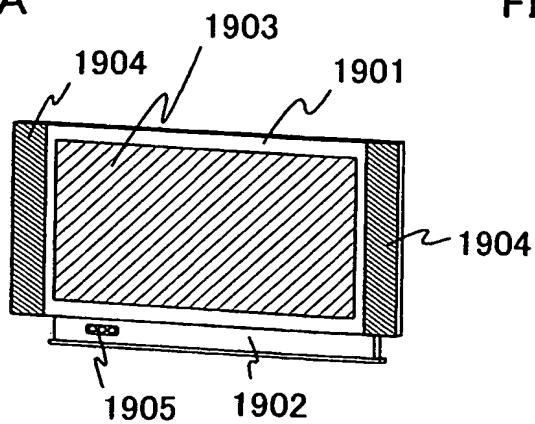


FIG. 19B

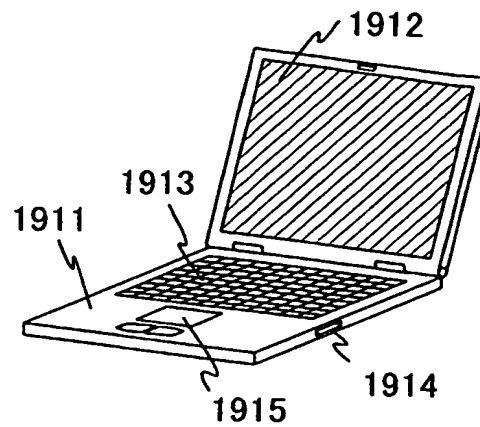


FIG. 19C

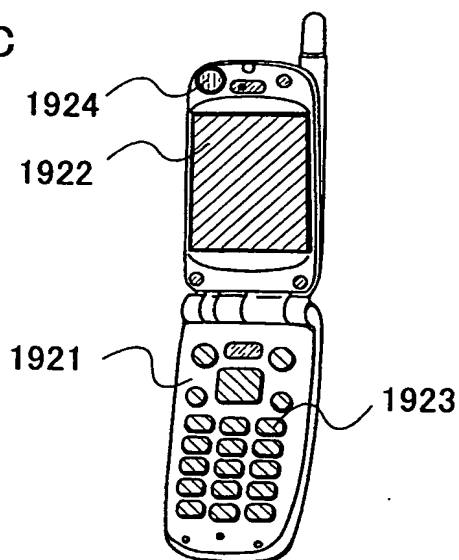


FIG. 19D

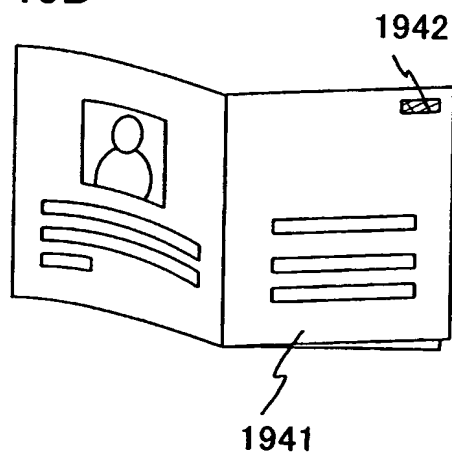
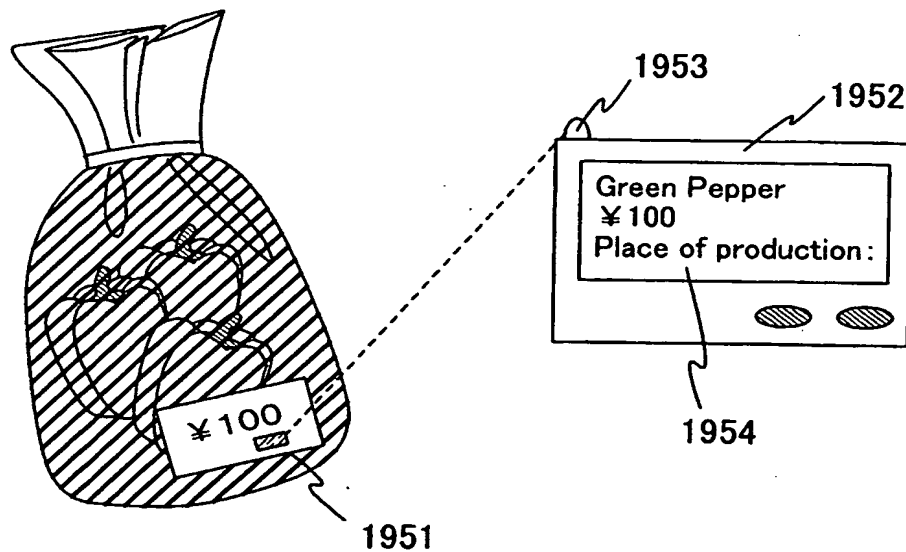


FIG. 19E



EXPLANATION OF REFERENCE

10: substrate, 11: base insulating film, 12: amorphous semiconductor film (semiconductor film having amorphous structure), 13: irradiation region, 14: crystalline semiconductor film (semiconductor film having crystalline structure), 15: arrow, 16: laser light, 17: semiconductor layer, 18: gate insulating film, 19: gate electrode, 20: source region, 21: drain region, 22: channel forming region, 23: interlayer insulating film, 24: source electrode, 25: drain electrode, 26: first LDD region, 27: second LDD region, 28: protective film, 29a: upper layer, 29b: lower layer, 30a: optical system, 30b: optical system, 31a: source region, 31b: drain region, 32: channel forming region, 33a: first interlayer insulating film, 33b: second interlayer insulating film, 36: first LDD region, 37: second LDD region, 38a: first gate insulating film, 38b: second gate insulating film, 39: gate electrode, 101: laser oscillator, 102: slit, 103: mirror, 104: first cylindrical lens, 105: second cylindrical lens, 106: semiconductor film, 107: substrate fixing stage, 108: X stage, 109: Y stage, 110: laser beam, 111: beam irradiation region, 610: substrate, 616: planarizing insulating film, 623: first electrode, 624: layer containing organic compound, 625: second electrode, 626: transparent protective layer, 627: transparent filler, 628: sealing agent, 629: insulator, 631: anisotropic conductive film, 632: FPC, 633: sealing substrate, 636: n-channel TFT, 637: p-channel TFT, 710: substrate having insulating surface, 711: base insulating film, 712: lower electrode, 713: first insulating film, 714: second insulating film, 715: channel forming region, 716: source region, 717: drain region, 718: second gate insulating film, 719a: first low-concentration impurity region, 719b: second low-concentration impurity region, 720a: upper layer of upper electrode, 720b: lower layer of upper electrode, 721: insulating film, 722: insulating film, 723: source wiring, 724: drain wiring, 1201: source-side driving circuit, 1202: pixel portion, 1203: gate-side driving circuit, 1204: sealing substrate, 1205: sealing agent, 1207: connecting region, 1208: terminal portion, 1209: FPC, 1210: substrate, 1301: driving IC, 1302: pixel portion, 1304: sealing substrate, 1305: sealing agent, 1307: connecting region, 1308: terminal portion, 1309: FPC, 1310: substrate, 1400: substrate, 1401: base insulating film, 1402: amorphous semiconductor film, 1405: laser light, 1406a: island-shaped semiconductor layer, 1406b: island-shaped semiconductor layer,

1406c: island-shaped semiconductor layer, 1406d: island-shaped semiconductor layer,
1406e: island-shaped semiconductor layer, 1408: gate insulating film, 1409a:
conductive film, 1409b: conductive film, 1410: resist mask, 1413: gate length, 1415:
resist mask, 1416a: impurity region, 1416b: impurity region, 1416c: impurity region,
5 1417: resist mask, 1418a: impurity region, 1418b: impurity region, 1419a: side wall,
1419b: sidewall, 1419c: sidewall, 1420a: high concentration impurity region, 1420b: high
concentration impurity region, 1420c: high concentration impurity region, 1421: resist
mask, 1422: first interlayer insulating film, 1423: second interlayer insulating film,
1425a: wiring, 1425b: wiring, 1425c: wiring, 1425d: wiring, 1425e: wiring, 1500: first
10 substrate, 1501: peeling layer, 1502: base insulating film, 1503: semiconductor film,
1504: semiconductor film having crystalline structure, 1506: island-shaped
semiconductor layer, 1507: island-shaped semiconductor layer, 1508: island-shaped
semiconductor layer, 1509: gate insulating film, 1510: gate electrode, 1511: gate
electrode, 1512: gate electrode, 1513: resist, 1515: resist, 1516: low-concentration
15 impurity region, 1517: low-concentration impurity region, 1518: resist, 1520:
high-concentration impurity region, 1521: insulating film, 1522: sidewall, 1523: sidewall,
1524: sidewall, 1526: resist, 1527: high concentration impurity region, 1528: high
concentration impurity region, 1530: n-channel TFT, 1531: p-channel TFT, 1532:
n-channel TFT, 1533: first interlayer insulating film, 1534: second interlayer insulating
20 film, 1535: wiring, 1536: wiring, 1537: wiring, 1538: wiring, 1539: wiring, 1541: third
interlayer insulating film, 1542: antenna, 1545: protective layer, 1546: groove, 1550:
adhesive agent, 1551: second substrate, 1552: adhesive agent, 1553: cover material,
1600: glass substrate, 1601: arithmetic logic unit, 1602: arithmetic logic unit
controller, 1603: instruction decoder, 1604: interrupt controller, 1605: timing controller,
25 1606: resistor, 1607: register controller, 1608: bus interface, 1609: ROM, 1620: ROM
interface, 1621: CLK 1, 1622: CLK 2, 1901: casing, 1902: support, 1903: display portion,
1904: speaker portion, 1905: video input terminal, 1911: casing, 1912: display portion,
1913: keyboard, 1914: external connection port, 1915: pointing mouse, 1921: casing,
1922: display portion, 1923: operation keys, 1924: sensor portion, 1941: passport, 1942:
30 radio frequency IC tag, 1951: radio frequency IC tag, 1952: reader, 1953: antenna

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portion, 1954: display portion